NSN 5961-01-050-7917

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-050-7917 **Inclosure Material:** Glass and metal **Overall Length:** 0.190 inches **Overall Diameter:** Between 0.592 inches and 0.660 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Gate **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 repetitive peak reverse voltage **Current Rating Per Characteristic:** 12.00 amperes forward current, total rms watts **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 110.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 82577-925947 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 3 ribbon Shelf Life: N/a **Unit Of Measure:** Demilitarization: No Fiig: